

# DN3134KT N-Channel Enhancement Mode Field Effect Transistor

# **General description**

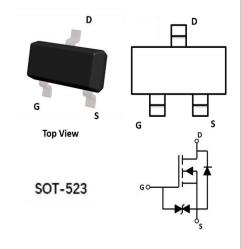
N-Channel Enhancement Mode Field Effect Transistor

#### Features:

- V<sub>DS</sub>: 20VI<sub>D</sub>: 0.75A
- $R_{DS(ON)}$ ( at  $V_{GS}$ =4.5V) < 270 mohm
- $R_{DS(ON)}$ ( at  $V_{GS}$ =2.5V) < 330 mohm

## **Applications**

- Drivers: Relays, Solenoid, Lamps, Hammers, Displays, Memories
- · Battery Operated Systems
- Power Supply Converter Circuits
- Load/Power Switching Cell Phones, Pagers



# **Device Marking Code:**

Device Type	Device Marking
DN3134KT	34K or 34

## **Absolute Maximum Ratings** (TA=25°Cunless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-source Voltage	VDS	20	V
Gate-source Voltage	Vgs	±8	V
Continuous Drain Current	lo	750	mA
Pulsed Drain Current <sup>A</sup>	Ірм	1000	mA
Power Dissipation with no heat sink @ T <sub>A</sub> =25 °C	P <sub>D</sub>	150	mW
Maximum Power Dissipation with infinite heat sink @ $T_{\text{C}}\text{=}25^{\circ}\!$		275	mW
Thermal Resistance From Junction To Ambient	R <sub>thJA</sub>	833	°C/W
Operation Junction Temperature	TJ	150	$^{\circ}$
Storage Temperature	Тѕтс	-55~+150	$^{\circ}$

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# **DN3134KT**



# Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> =250μA 20				V
Zero gate voltage drain current	IDSS	V <sub>DS</sub> =20V,V <sub>GS</sub> =0V			1	μA
Gate-body leakage current	IGSS1	V <sub>GS</sub> = ±8V, V <sub>DS</sub> =0V			±10	μA
Gate threshold voltage	V <sub>G</sub> S(th)	$V_{DS}=V_{GS}, I_{D}=250\mu A$	0.45	0.75	1.2	V
Drain-source on-resistance		V <sub>GS</sub> = 4.5V, I <sub>D</sub> =750mA		220	300	mΩ
	RDS(ON)	VGS= 2.5V, ID=400mA		260	400	
Dynamic characteristics <sup>B</sup>						
Input Capacitance	Ciss			21		pF
Output Capacitance	Coss	V <sub>DS</sub> =15V,V <sub>GS</sub> =0V,f=1MHZ		15		
Reverse Transfer Capacitance	Crss			8		
Switching Characteristics <sup>B</sup>						
Turn-on delay time	td(on)	V <sub>GS</sub> =4.5V,V <sub>DD</sub> =10V,R <sub>G</sub> =10Ω,I <sub>D</sub> =50		6.7		
Turn-on rise time	t <sub>r</sub>	0mA		4.8		- ns
Turn-off delay time	td(off)			17.3		
Turn-off fall time	t <sub>f</sub>			7.4		
Source-Drain Diode characteristics						
Diode Forward voltage <sup>c</sup>	VDS	V <sub>GS</sub> =0V,I <sub>S</sub> =150mA			1.2	V

### Notes:

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A. Repetitive Rating: Pulse width limited by maximum junction temperature.

B. These parameters have no way to verify.

C. Pulse Test: Pulse Width  $\leq$  300us, Duty Cycle  $\leq$  0.5%.

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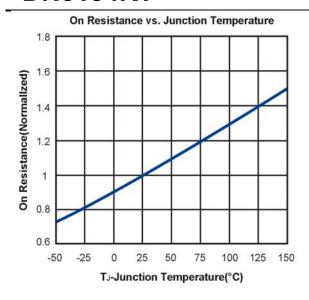


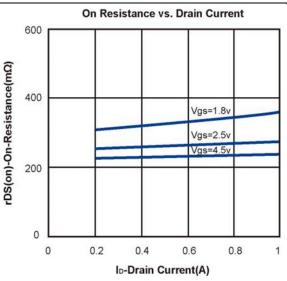
**Typical Performance Characteristics** 

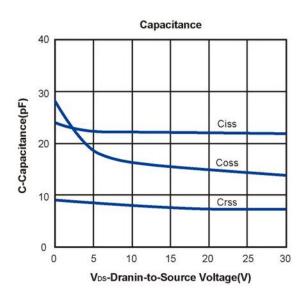
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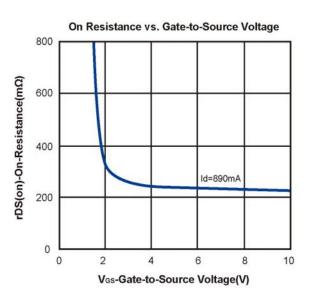
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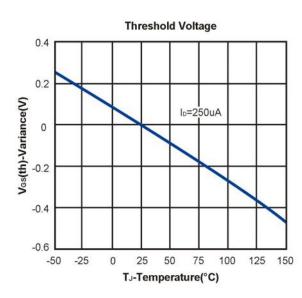


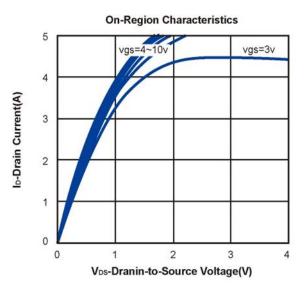








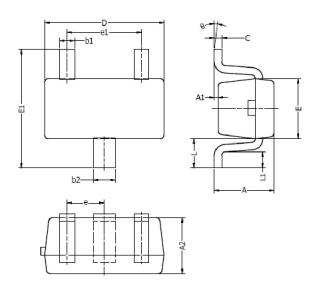




**SOT-523 Package Outline** 

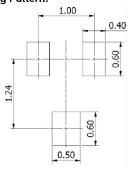
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DIM	MILLIMETERS		INCHES		
DIIVI	MIN	MAX	MIN	MAX	
A	0.70	0.90	0.028	0.035	
A1	0.00	0.10	0.000	0.004	
A2	0.70	0.80	0.028	0.031	
b1	0.15	0.25	0.006	0.010	
b2	0.25	0.35	0.010	0.014	
С	0.10	0.20	0.004	0.008	
D	1.50	1.70	0.059	0.067	
E	0.70	0.90	0.028	0.035	
E1	1.45	1.75	0.057	0.069	
е	0.50	0.50 TYP.		TYP.	
e1	0.90	1.10	0.035	0.043	
L	0.40 REF.		0.016 REF.		
L1	0.10	0.30	0.004	0.012	
θ	O°	8°	O°	8°	

# Typical Soldering Pattern:



### Note

- 1. Above package outline conforms to JEITA EAIJ ED-7500A SC-75A.
- 2.Dimensions are exclusive of Burrs, Mold Flash & Tie Bar extrusions.

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